ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor device wherein the lower portion of a contact hole is cleaned, and doped with an impurity for reducing contact resistance is disclosed. The method comprises: sequentially forming a buffer layer and an interlayer insulating film on a semiconductor substrate; etching the interlayer insulating film and the buffer layer to form a contact hole exposing the semiconductor substrate; performing a cleaning process of a lower portion of the contact hole; doping an impurity into the surface of the semiconductor substrate exposed by the contact hole; and forming a conductive layer filling the contact hole on the entire surface of the resulting structure.